Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	6	(("5637884") or ("5811324")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/06/16 15:17
S2	6	(("4979014") or ("5466621")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/07 14:38
S3	382	(257/900).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/07 14:39
S4	378	((257/900).CCLS.) and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/26 09:35
S5	234007	(("257") or ("438")).CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/07 14:44
S6	682	((("257"/$) or ("438"/$)).CCLS.) and @ad<="20000731" and 'convex' with 'layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 14:49
S7	1	"5095347".PN.	USPAT	OR	OFF	2002/05/07 14:46
S8	1	"5095347".PN.	USPAT	OR	OFF	2002/05/07 14:46
S9	1	"5120666".PN.	USPAT	OR	OFF	2002/05/07 14:46
S10	1	"4774196".PN.	USPAT	OR	OFF	2002/05/07 14:46
S11	1	"5410172".PN.	USPAT	OR	OFF	2002/05/07 14:47
S12	1	"5420055".PN.	USPAT	OR	OFF	2002/05/07 14:47
S13	1	"5578513".PN.	USPAT	OR	OFF	2002/05/07 14:47
S14	1	"5580802".PN.	USPAT	OR	OFF	2002/05/07 14:48
S15	610	((("257"/$) or ("438"/$)).CCLS.) and @ad<="20000731" and 'convex' with 'semiconductor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 14:51
S16	0	((("257"/$) or ("438"/$)).CCLS.) and @ad<="20000731" and 'convex semiconductor' and 'side-wall gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 14:52

S17	0	(((("257"/$) or ("438"/$)).CCLS.) and @ad<="20000731" and 'convex semiconductor' and 'side wall gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 14:53
S18	1531	(((("257"/$) or ("438"/$)).CCLS.) and @ad<="20000731" and 'side wall gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 14:57
S19	40	((((("257"/$) or ("438"/$)).CCLS.) and @ad<="20000731" and 'side wall gate') and 'convex'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 15:09
S20	238	(257/394).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/07 15:12
S21	232	(257/394).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 15:43
S22	1	"4979014".PN.	USPAT	OR	OFF	2002/05/07 15:30
S23	1	"5463241".PN.	USPAT	OR	OFF	2002/05/07 15:30
S24	1	"5512770".PN.	USPAT	OR	OFF	2002/05/07 15:31
S25	156	(257/262).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 15:56
S26	17	'trench isolated transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 15:57
S27	17	trench adj isolated adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/24 16:39
S28	1	"4449285".PN.	USPAT	OR	OFF	2002/05/07 15:59
S29	1	"4606011".PN.	USPAT	OR	OFF	2002/05/07 15:59
S30	1	"4670768".PN.	USPAT	OR	OFF	2002/05/07 15:59
S31	1	"4449285".PN.	USPAT	OR	OFF	2002/05/07 16:09
S32	1	"4606011".PN.	USPAT	OR	OFF	2002/05/07 16:09
S33	1	"4670768".PN.	USPAT	OR	OFF	2002/05/07 16:09
S34	1	"4801988".PN.	USPAT	OR	OFF	2002/05/07 16:11
S35	1	"4833516".PN.	USPAT	OR	OFF	2002/05/07 16:11
S36	1	"4910567".PN.	USPAT	OR	OFF	2002/05/07 16:11

S37	1	"5013679".PN.	USPAT	OR	OFF	2002/05/07 16:12
S38	1	"5013679".PN.	USPAT	OR	OFF	2002/05/07 16:12
S39	1	"5264716".PN.	USPAT	OR	OFF	2002/05/07 16:12
S40	1	"5289027".PN.	USPAT	OR	OFF	2002/05/07 16:12
S41	1	"5348905".PN.	USPAT	OR	OFF	2002/05/07 16:13
S42	1	"5360758".PN.	USPAT	OR	OFF	2002/05/07 16:13
S43	1	"5404037".PN.	USPAT	OR	OFF	2002/05/07 16:13
S44	1	"5567962".PN.	USPAT	OR	OFF	2002/05/07 16:13
S45	1	"5567962".PN.	USPAT	OR	OFF	2002/05/07 16:13
S46	1	"5567962".PN.	USPAT	OR	OFF	2002/05/07 16:14
S47	1	"5675164".PN.	USPAT	OR	OFF	2002/05/07 16:14
S48	1	"5909044".PN.	USPAT	OR	OFF	2002/05/07 16:15
S49	1	"5990510".PN.	USPAT	OR	OFF	2002/05/07 16:15
S50	1	"5994197".PN.	USPAT	OR	OFF	2002/05/07 16:15
S51	1	"5994729".PN.	USPAT	OR	OFF	2002/05/07 16:15
S52	1	"5998820".PN.	USPAT	OR	OFF	2002/05/07 16:16
S53	1	"5998821".PN.	USPAT	OR	OFF	2002/05/07 16:16
S54	1	"6008513".PN.	USPAT	OR	OFF	2002/05/07 16:16
S55	1	"6020609".PN.	USPAT	OR	OFF	2002/05/07 16:17
S56	1	"6025620".PN.	USPAT	OR	OFF	2002/05/07 16:17
S57	1	"6037210".PN.	USPAT	OR	OFF	2002/05/07 16:17
S58	2781	side adj wall adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 16:26
S59	46	(side adj wall adj gate) and @ad<="20000731" and 'convex'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:36
S60	80	'side-wall' adj gates	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 16:27
S61	77	('side-wall' adj gates) and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/07 16:43
S62	24	'convex semiconductor layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 07:58

S63	24	'convex semiconductor layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/24 16:38
S64	1	"3278789".PN.	USPAT	OR	OFF	2002/05/08 08:10
S65	1	"3663857".PN.	USPAT	OR	OFF	2002/05/08 08:10
S66	1	"3735186".PN.	USPAT	OR	OFF	2002/05/08 08:10
S67	1	"4093562".PN.	USPAT	OR	OFF	2002/05/08 08:10
S68	1	"4325084".PN.	USPAT	OR	OFF	2002/05/08 08:10
S69	1	"5066883".PN.	USPAT	OR	OFF	2002/05/08 08:11
S70	1	"3805123".PN.	USPAT	OR	OFF	2002/05/08 08:11
S71	1	"5753966".PN.	USPAT	OR	OFF	2002/05/08 08:11
S72	1	"5753966".PN.	USPAT	OR	OFF	2002/05/08 08:12
S73	1	"5814532".PN.	USPAT	OR	OFF	2002/05/08 08:12
S74	1	"5972730".PN.	USPAT	OR	OFF	2002/05/08 08:12
S75	1	"6037210".PN.	USPAT	OR	OFF	2002/05/08 08:31
S76	1	"6025620".PN.	USPAT	OR	OFF	2002/05/08 08:31
S77	1	"6020609".PN.	USPAT	OR	OFF	2002/05/08 08:31
S78	1	"5998821".PN.	USPAT	OR	OFF	2002/05/08 08:31
S79	155	'projection' near 'semiconductor substrate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 08:46
S80	143	('projection' near 'semiconductor substrate') and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 09:54
S81	799	(257/192).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:57
S82	403	((257/192).ccls. and @ad<="20000731") and 'FET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:00
S83	201	(257/386).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:17
S84	244	(257/387).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:26

S85	111	(257/388).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:32
S86	149	(257/389).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:37
S87	259	(257/393).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:39
S88	315	(257/346).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:43
S89	93	(257/395).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:47
S90	67	(257/27).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:49
S91	206	(257/69).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:54
S92	39	(438/247).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 10:59
S93	86	(438/159).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 11:01
S94	177	(438/155).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/08 11:03
S95	139	(257/348).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:16

S96	173	'surrounding gate transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/25 16:01
S97	1842	(257/296).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/02 10:31
S98	4811	((257/296) or (257/306) or (257/530) or (257/354) or (438/238-239)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/02/26 09:44
S99	542	((257/296).ccls. and @ad<="20000731") and 'surrounding gate transistor' or 'SGT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/26 09:42
S100	166	'surrounding gate transistor' and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 06:07
S101	87	'gate electrode' with 'electric field effect'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/04 09:59
S102	275	'gate electrode applying'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/04 10:02
S103	39	'gate electrode applying' with 'electric field'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/04 10:07
S104	2	'gate electrode applying' with 'electric field' with 'channel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/04 10:10
S105	87	'gate electrode applying' and 'electric field' and 'channel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/04 10:11
S106	196	'surrounding gate transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/24 15:49

S10 7	1	"4979014".PN.	USPAT	OR	OFF	2003/02/26 09:03
S10 8	1	"5019878".PN.	USPAT	OR	OFF	2003/02/26 09:03
S10 9	1	"5089870".PN.	USPAT	OR	OFF	2003/02/26 09:04
S11 0	1	"5115289".PN.	USPAT	OR	OFF	2003/02/26 09:04
S11 1	1	"5163180".PN.	USPAT	OR	OFF	2003/02/26 09:06
S11 2	2	("5424227").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/02/26 09:30
S11 3	828	((257/192).CCLS.) and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/16 15:40
S11 4	46	((257/196).CCLS.) and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/26 09:35
S11 5	577	((257/296).ccls. and @ad<="20000731") and 'surrounding gate transistor' or 'SGT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/26 09:44
S11 6	23	((257/296).ccls. and @ad<="20000731") and 'surrounding gate transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/02/26 09:44
S11 7	5205	((257/296) or (257/306) or (257/530) or (257/354) or (438/238-239)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/02/26 09:49
S11 8	4	(("5670810") or ("5414287")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/02/26 11:04
S11 9	2	"20020011612"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/16 15:17

S12 0	506	@ad<="20000731" and 'SGT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 12:41
S12 1	174	@ad<="20000731" and surrounding adj1 gate adj1 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:19
S12 2	70	@ad<="20000731" and 'SGT' and ("257"/$).ccls. and ("438"/$).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/17 08:07
S12 3	1037	(257/401).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 07:42
S12 4	43	(438/284).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/06/17 08:23
S12 5	2	("20020011612").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/24 15:31
S12 6	2	("5466621").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/24 15:31
S12 7	178	@ad<="20000731" and 'surrounding gate transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:41
S12 8	32	'convex semiconductor layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/24 16:40
S12 9	687	'SGT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/24 16:41
S13 0	55	@ad<="20000731" and 'sgt' and 'side wall'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 06:12

S13 1	8	'surrounding gate transistor' and @ad<="20000731" and 'offset' with 'gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 06:07
S13 2	180	@ad<="20000731" and 'surrounding gate transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 06:12
S13 3	48	@ad<="20000731" and 'sgt' and 'offset'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/29 12:12
S13 4	2	@ad<="20000731" and 'sgt' and 'offset' with 'sidewall'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 06:13
S13 5	496	(257/328).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:20
S13 6	181	(257/263).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 07:43
S13 7	367	(257/302).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:40
S13 8	158	(257/348).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:16
S13 9	166	(257/262).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:24
S14 0	181	(257/263).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:24
S14 1	1394	(257/347).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:41

S14 2	83	@ad<="20000731" and 'surrounding' adj1 'channel' adj1 'region'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:42
S14 3	180	@ad<="20000731" and surrounding adj1 gate adj1 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 08:42
S14 4	395	(257/900).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 09:25
S14 5	1050	(257/401).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 09:27
S14 6	326	(257/618).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 09:45
S14 7	296	(257/402).ccls. and @ad<="20000731"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/14 09:28
S14 8	9	@ad<="20000731" and 'gate oxide' same 'silicon oxide' with 'titanium oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/29 12:15
S14 9	11	@ad<="20000731" and 'gate oxide' same 'silicon oxide' same 'titanium oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/29 12:17
S15 0	11	@ay<="2000" and 'gate oxide' same 'silicon oxide' same 'titanium oxide'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/29 12:18
S15 1	11	@ad<="20000731" and 'SGT' same 'trench capacitor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 12:52
S15 2	112	@ad<="20000731" and 'SGT' same 'DRAM'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:20

S15 3	0	@ad<="20000731" and 'FIN' near 'FET' same 'trench capacitor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:16
S15 4	0	@ad<="20000731" and 'FIN' adj1 'FET' same 'trench capacitor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:17
S15 5	12	@ad<="20000731" and 'FIN' adj1 'FET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:18
S15 6	6	@ad<="20000731" and 'FINFET'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:18
S15 7	181	@ad<="20000731" and 'surrounding gate transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:20
S15 8	36	@ad<="20000731" and 'SGT' same 'capacitor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:37
S15 9	0	@ad<="20000731" and "Katsuhiko-Hieda.in"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:38
S16 0	1	@ad<="20000731" and Katsuhiko-Hieda.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:38
S16 1	195	@ad<="20000731" and hieda-katsuhiko.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/27 13:38
S16 3	10	(("5466621") or ("5346834") or ("5115289") or ("6525403") or ("6300664") or ("5336638") or ("6525403")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/20 09:28
S16 4	1	"20010002719".PN.	US-PGPUB	OR	ON	2005/09/20 09:15
S16 5	1	"6373123".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:17

S16 6	1	"6246090".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:18
S16 7	1	"6229161".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:18
S16 8	1	"6191432".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:18
S16 9	1	"5942768".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:19
S17 0	1	"5844278".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:19
S17 1	1	"5466621".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:19
S17 2	1	"5338942".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:20
S17 3	1	"4764799".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:21
S17 4	1	"4296428".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:21
S17 5	1	"3893152".PN.	USPAT; USOCR	OR	ON	2005/09/20 09:21
S17 6	2	("4979014").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/20 09:28
S17 7	23	@ad<="20010730" and 'finfet'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:37
S17 9	46	@ad<="20010730" and 'finfet' or (folded-channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:40
S18 0	333	@ad<="20010730" and 'finfet' or 'folded-channel' or 'surrounding gate transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:43
S18 1	7	@ad<="20010730" and 'folded-channel'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:41
S18 2	7	@ad<="20010730" and (folded-channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:41

S18 3	209	@ad<="20010730" and 'surrounding gate transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:44
S18 4	597	@ad<="20010730" and 'sgt'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:44
S18 5	166	@ad<="20010730" and 'surrounded gate' with 'transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:45
S18 6	21	@ad<="20010730" and 'surrounded gate' with 'fet'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:45
S18 7	24	@ad<="20010730" and 'surrounding gate' with 'fet'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:45
S18 9	316	@ad<="20010730" and 'surrounding gate' with 'transistor'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 09:45